



60V DUAL NPN LOW SATURATION TRANSISTOR IN SOT26

Features

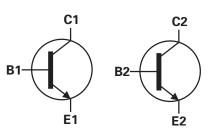
- BV_{CEO} > 60V
- I_C = 1A high Continuous Collector Current
- I_{CM} = 2A Peak Pulse Current
- $R_{CE(sat)} = 100 \text{m}\Omega$ for a Low Equivalent On-Resistance
- Low Saturation Voltage V_{CE(sat)} < 250mV @ 1A
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

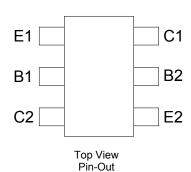
- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208
- Weight: 0.015 grams (approximate)







Device Symbol



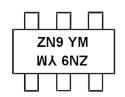
Ordering Information (Note 4)

Ī	Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	DSS4160DS-7	ZN9	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



ZN9 = Product Type Marking Code YM = Date Code Marking Y = Year ex: A = 2013 M = Month ex: 9 = September

Date Code Key

Year	2013	20	014	2015	2	2016	2017		2018	2019		2020
Code	Α		В	С		D	Е		F	G		Н
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



Absolute Maximum Ratings - Q1 & Q2 Common (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	I _C	1	Α
Peak Pulse Collector Current	Ісм	2	Α
Base current	I _B	300	mA
Peak Pulse Base current	Івм	1	Α

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Notes 5 & 9)		0.7 5.6		
	(Notes 6 & 9)	P _D	0.9 7.2		
Power Dissipation Linear Derating Factor	(Notes 6 & 10)		1.1 8.8	W mW/°C	
	(Notes 7 & 9)		1.1 8.8		
	(Notes 8 & 9)		1.7 13.6		
	(Notes 5 & 9)		179		
	(Notes 6 & 9)	$R_{ hetaJA}$	139		
Thermal Resistance, Junction to Ambient	(Notes 6 & 10)		113	2004	
	(Notes 7 & 9)		113	°C/W	
	(Notes 8 & 9)		73		
Thermal Resistance, Junction to Lead	(Note 11)	$R_{ heta JL}$	96		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 12)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

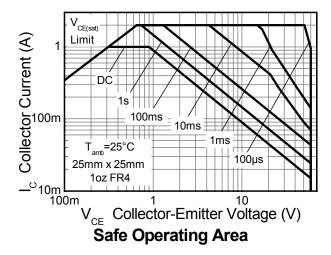
 6. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.

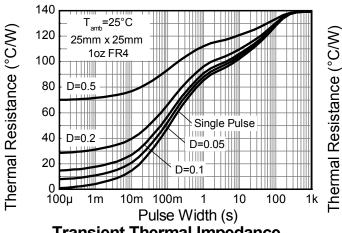
 7. Same as note (5), except the device is mounted on 50mm x 50mm 2oz copper.

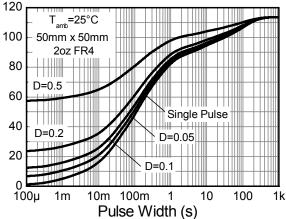
- 8. Same as note (7), except the device is measured at t < 5 seconds. 9. One active die operating with the collector attached to the heatsink.
- 10. Two active dice running at equal power with heatsink split 50% to each collector.
- 11. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 12. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information

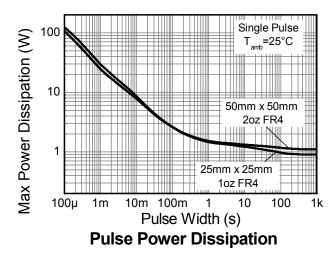


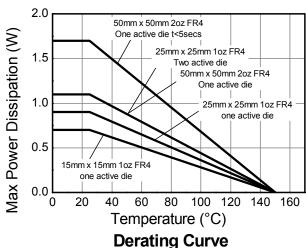




Transient Thermal Impedance









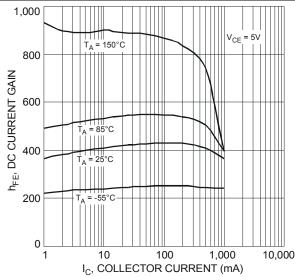
Electrical Characteristics - Q1 & Q2 common (@T_A = +25°C, unless otherwise specified.)

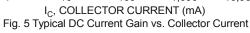
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	80	_	_	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 13)	BV _{CEO}	60	_	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV_EBO	5	_	_	V	I _E = 100μA
Collector-Base Cutoff Current	lone	_	_	100	nA	$V_{CB} = 60V, I_{E} = 0A$
Collector-base Cuton Current	I _{CBO}	_	_	50	μΑ	$V_{CB} = 60V, I_E = 0A, T_J = +150^{\circ}C$
Collector-Emitter Cutoff Current	I _{CES}	_	_	100	nA	V _{CES} = 60V, V _{BE} = 0V
Emitter-Base Cutoff Current	I _{EBO}	_	_	100	nA	$V_{EB} = 5V$, $I_C = 0A$
		250	380	_		I _C = 1mA, V _{CE} = 5V
DC Current Gain (Note 13)	h_{FE}	200	420	_	_	$I_C = 500 \text{mA}, V_{CE} = 5 \text{V}$
		100	380	_		I _C = 1A, V _{CE} = 5V
		_	60	110		$I_C = 100 \text{mA}, I_B = 1 \text{mA}$
Collector-Emitter Saturation Voltage (Note 13)	$V_{CE(sat)}$	_	70	140	mV	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
		_	100	250		I _C = 1A, I _B = 100mA
Equivalent On-Resistance	R _{CE(sat)}	_	100	250	mΩ	I _C = 1A, I _B = 100mA
Base-Emitter Saturation Voltage (Note 13)	$V_{BE(sat)}$	_	940	1100	mV	$I_C = 1A$, $I_B = 50mA$
Base-Emitter Turn-On Voltage (Note 13)	$V_{BE(on)}$	_	780	900	mV	$I_C = 1A$, $V_{CE} = 5V$
Output Capacitance	C_obo	_	5.5	10	pF	V _{CB} = 10V, f = 1MHz
Transition Frequency	f _T	150	220	_	MHz	$V_{CE} = 10V, I_{C} = 50mA$ f = 100MHz
Turn-On Time	t _{on}	_	63	_	ns	
Delay Time	t _d	_	33	_	ns	
Rise Time	t _r	_	30	_	ns	$V_{CC} = 10V, I_C = 0.5A$
Turn-Off Time	t _{off}	_	420	_	ns	I _{B1} = -I _{B2} = 25mA
Storage Time	t _s	_	380	_	ns]
Fall Time	t _f	_	40		ns	

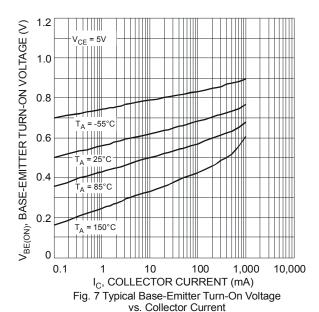
Notes: 13. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%

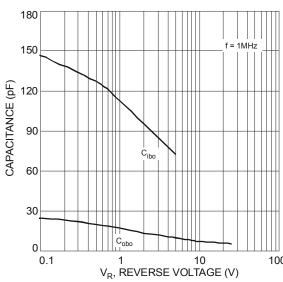


Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

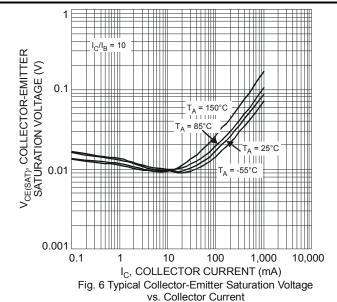


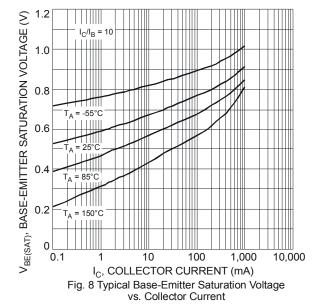






100 Fig. 9 Typical Capacitance Characteristics

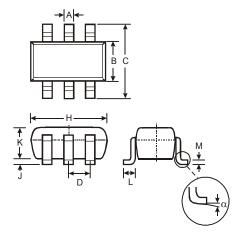






Package Outline Dimensions

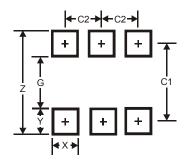
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT26						
Dim	Min	Max	Тур				
Α	0.35	0.50	0.38				
В	1.50	1.70	1.60				
С	2.70	3.00	2.80				
D	_		0.95				
Н	2.90	3.10	3.00				
J 0.013		0.10	0.05				
K	1.00	1.30	1.10				
L	0.35	0.55	0.40				
M	0.10	0.20	0.15				
α	0°	8°	_				
All D	All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Υ	0.80
C1	2.40
C2	0.95



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2013, Diodes Incorporated

www.diodes.com